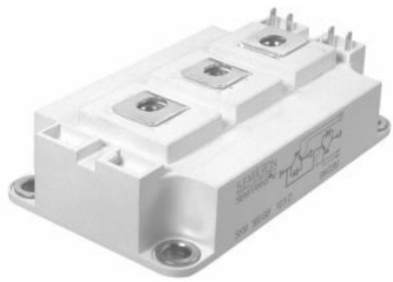
Absolute Maximum Ratings Symbol	Conditions [1]	Values		Units
V_{CES}		1200		V
V_{CGR}	R_{GE} = 20 kΩ	1200		V
I_C	T_{case} = 25/80 °C	300 / 220		A
I_{CM}	T_{case} = 25/80 °C; t_p = 1 ms	600 / 440		A
V_{GES}		± 20		V
P_{tot}	per IGBT, T_{case} = 25 °C	1660		W
T_j, (T_{stg})		– 40 . . .+150 (125)		°C
V_{isol}	AC, 1 min.	2 500		V
humidity	DIN 40 040	Class F		
climate	DIN IEC 68 T.1	40/125/56		
Inverse Diode			FWD [6]	
I_F= – I_C	T_{case} = 25/80 °C	260 / 180	350 / 230	A
I_{FM}= – I_{CM}	T_{case} = 25/80 °C; t_p = 1 ms	600 / 440	600 / 440	A
I_{FSM}	t_p = 10 ms; sin.; T_j = 150 °C	2200	2900	A
I^2t	t_p = 10 ms; T_j = 150 °C	24200	42000	A^2s

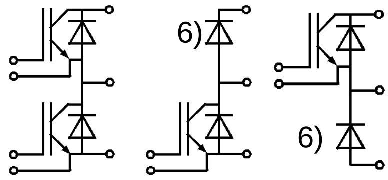
Characteristics Symbol	Conditions [1]	min.	typ.	max.	Units
$V_{(BR)CES}$	V_{GE} = 0, I_C = 4 mA	≥ V_{CES}	–	–	V
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 8 mA	4,5	5,5	6,5	V
I_{CES}	V_{GE} = 0 } T_j = 25 °C	–	3	4,5	mA
	V_{CE} = V_{CES} } T_j = 125 °C	–	15	–	mA
I_{GES}	V_{GE} = 20 V, V_{CE} = 0	–	–	0,4	µA
V_{CEsat}	I_C = 200 A { V_{GE} = 15 V;	–	2,5(3,1)	3(3,7)	V
V_{CEsat}	I_C = 300 A { T_j = 25 (125) °C	–	3(3,8)	–	V
g_{fs}	V_{CE} = 20 V, I_C = 200 A	108	150	–	S
C_{CHC}	per IGBT	–		700	pF
C_{ies}	} V_{GE} = 0	–	18	24	nF
C_{oes}	} V_{CE} = 25 V	–	2,5	3,2	nF
C_{res}	} f = 1 MHz	–	1,0	1,3	nF
L_{CE}		–	–	20	nH
$t_{d(on)}$	} V_{CC} = 600 V	–	250	400	ns
t_r	} V_{GE} = + 15 V / - 15 V [3]	–	90	160	ns
$t_{d(off)}$	} I_C = 200 A, ind. load	–	550	700	ns
t_f	} R_{Gon} = R_{Goff} = 4,7 Ω	–	70	100	ns
E_{on} [5]	} T_j = 125 °C	–	28	–	mWs
E_{off} [5]		–	26	–	mWs
Inverse Diode [8]					
V_F = V_{EC}	I_F = 200 A { V_{GE} = 0 V;	–	2,0(1,8)	2,5	V
V_F = V_{EC}	I_F = 300 A { T_j = 25 (125) °C	–	2,25(2,1)	–	V
V_{TO}	T_j = 125 °C [2]	–	1,1	1,2	V
r_T	T_j = 125 °C [2]	–	3	5,5	mΩ
I_{RRM}	I_F = 200 A; T_j = 25 (125) °C [2]	–	70(105)	–	A
Q_{rr}	I_F = 200 A; T_j = 25 (125) °C [2]	–	10(26)	–	µC
FWD of type "GAL" and "GAR" [8] [6]					
V_F = V_{EC}	I_F = 200 A { V_{GE} = 0 V;	–	1,9(1,7)	2,4	V
V_F = V_{EC}	I_F = 300 A { T_j = 25 (125) °C	–	2,1(1,8)	–	V
V_{TO}	T_j = 125 °C	–	–	1,2	V
r_T	T_j = 125 °C	–	3	3,5	mΩ
I_{RRM}	I_F = 200 A; T_j = 25 (125) °C [2]	–	80(140)	–	ns
Q_{rr}	I_F = 200 A; T_j = 25 (125) °C [2]	–	10(34)	–	µC
Thermal Characteristics					
R_{thjc}	per IGBT	–	–	0,075	°C/W
R_{thjc}	per diode / FWD [6]	–	–	0,18/0,15	°C/W
R_{thch}	per module	–	–	0,038	°C/W

SEMITRANS® M IGBT Modules

SKM 300 GB 123 D
SKM 300 GAL 123 D [6]
SKM 300 GAR 123 D [6]



SEMITRANS 3



GB **GAL** **GAR**

Features

- MOS input (voltage controlled)
- N channel, Homogeneous Si
- Low inductance case
- Very low tail current with low temperature dependence
- High short circuit capability, self limiting to 6 * I_{cnom}
- Latch-up free
- Fast & soft inverse CAL diodes[8]
- Isolated copper baseplate using DCB Direct Copper Bonding Technology
- Large clearance (12 mm) and creepage distances (20 mm).

Typical Applications: → B6-153

- Switching, not for linear use
- AC-inverter drives
- UPS

[1] T_{case} = 25 °C, unless otherwise specified

[2] I_F = – I_C, V_R = 600 V, – di_F/dt = 2000 A/µs, V_{GE} = 0 V

[3] Use V_{GEoff} = -5 ... -15 V

[5] see fig. 2 + 3; R_{Goff} = 4,7 Ω

[6] The free-wheeling diodes of the GAL and GAR types have the data of the inverse diodes of SKM 400 GA 123 D

[8] CAL = Controlled Axial Lifetime Technology.

Cases and mech. data → B6-174 SEMITRANS 3

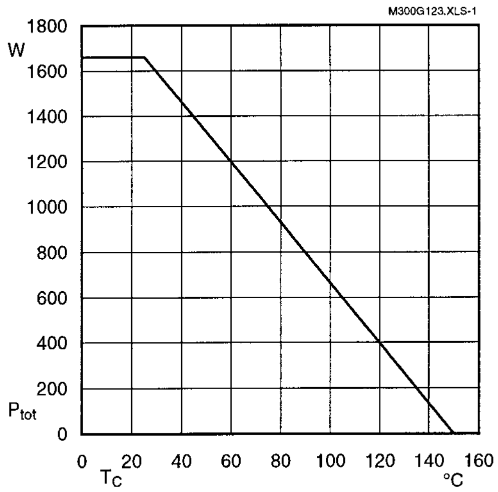
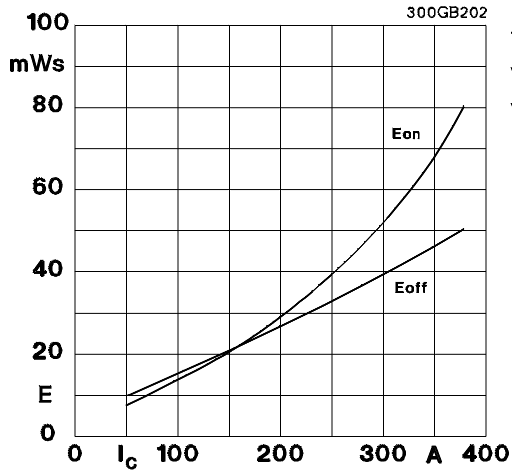
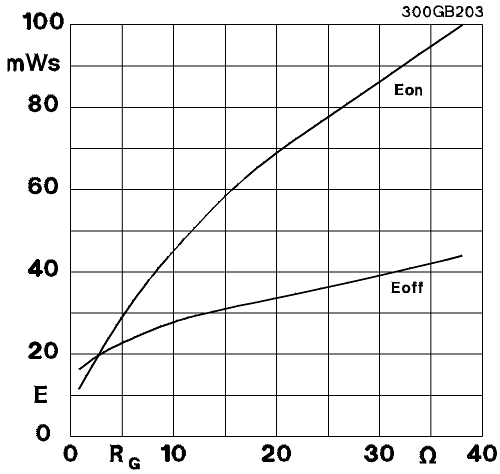


Fig. 1 Rated power dissipation $P_{tot} = f\ (T_C)$



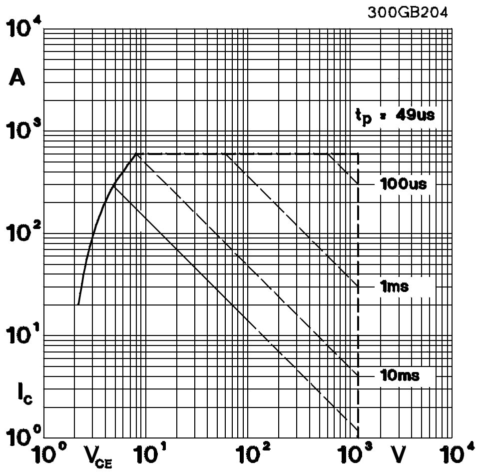
T_j = 125 °C
V_{CE} = 600 V
V_{GE} = ± 15 V
R_G = 4,7 Ω

Fig. 2 Turn-on /-off energy = f (I_C)



T_j = 125 °C
V_{CE} = 600 V
V_{GE} = ± 15 V
I_C = 200 A

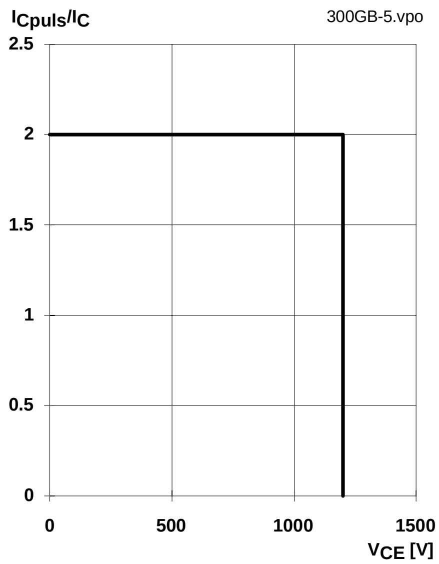
Fig. 3 Turn-on /-off energy = f (R_G)



1 pulse
T_C = 25 °C
T_j ≤ 150 °C

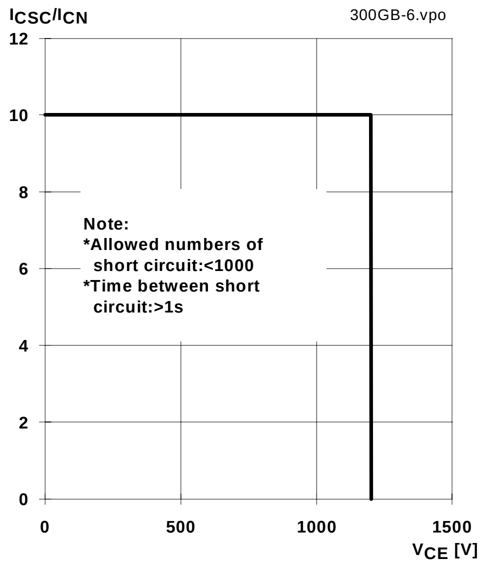
Not for
linear use

Fig. 4 Maximum safe operating area (SOA) $I_C = f\ (V_{CE})$



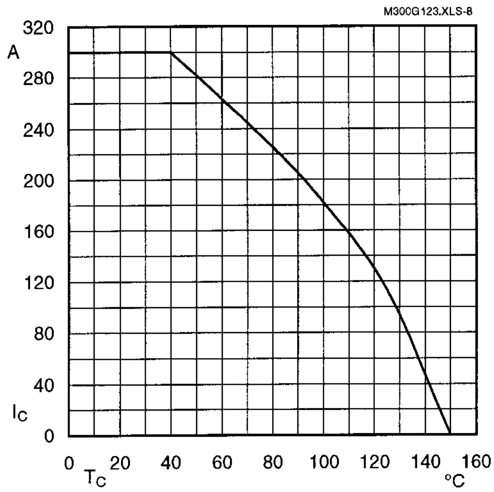
T_j ≤ 150 °C
V_{GE} = 15 V
R_{Goff} = 4,7 Ω
I_C = 200 A

Fig. 5 Turn-off safe operating area (RBSOA)



T_j ≤ 150 °C
V_{GE} = ± 15 V
t_{sc} ≤ 10 µs
L < 25 nH
I_{CN} = 200 A

Fig. 6 Safe operating area at short circuit $I_C = f\ (V_{CE})$



T_j = 150 °C
$V_{GE} \geq 15$ V

Fig. 8 Rated current vs. temperature $I_C = f\,(T_C)$

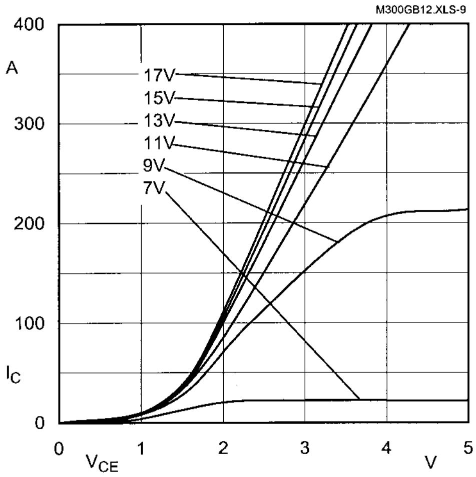


Fig. 9 Typ. output characteristic, t_p = 80 µs; 25 °C

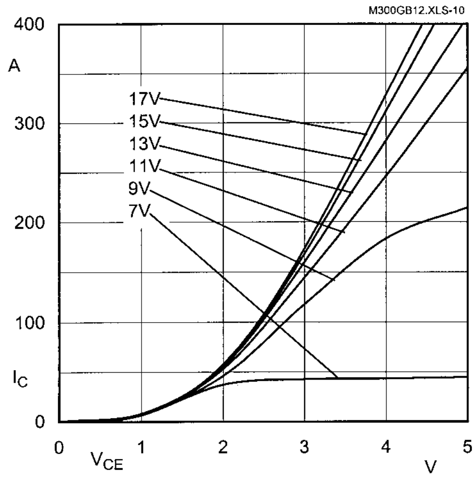


Fig. 10 Typ. output characteristic, t_p = 80 µs; 125 °C

$P_{cond(t)} = V_{CEsat(t)} \cdot I_{C(t)}$

$V_{CEsat(t)} = V_{CE(TO)(Tj)} + r_{CE(Tj)} \cdot I_{C(t)}$

$V_{CE(TO)(Tj)} \leq 1{,}5 + 0{,}002\ (T_j - 25)$ [V]

typ.: $r_{CE(Tj)} = 0{,}005 + 0{,}00002\ (T_j - 25)$ [Ω]

max.: $r_{CE(Tj)} = 0{,}0075 + 0{,}000025\ (T_j - 25)$ [Ω]

valid for $V_{GE} = +\,15\ {}^{+2}_{-1}$ [V]; $I_C > 0{,}3\ I_{Cnom}$

Fig. 11 Saturation characteristic (IGBT)
Calculation elements and equations

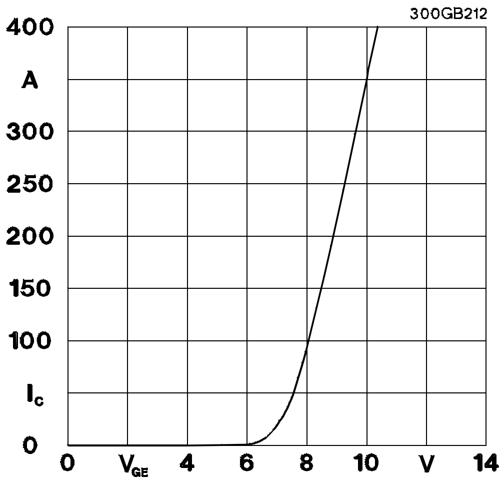
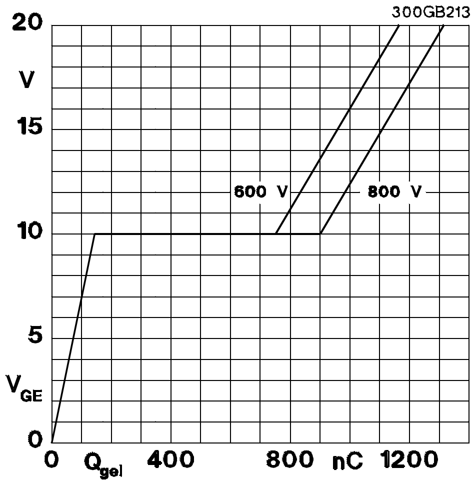
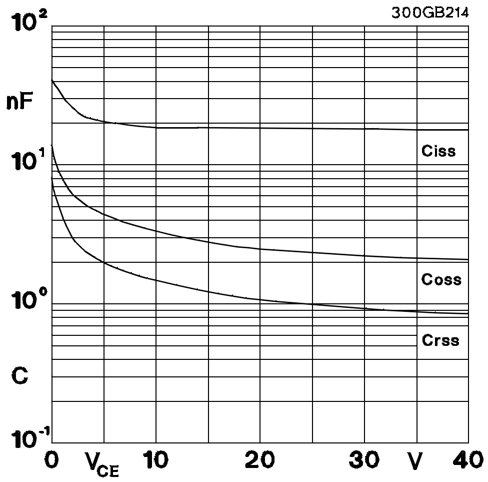


Fig. 12 Typ. transfer characteristic, t_p = 80 µs; V_{CE} = 20 V



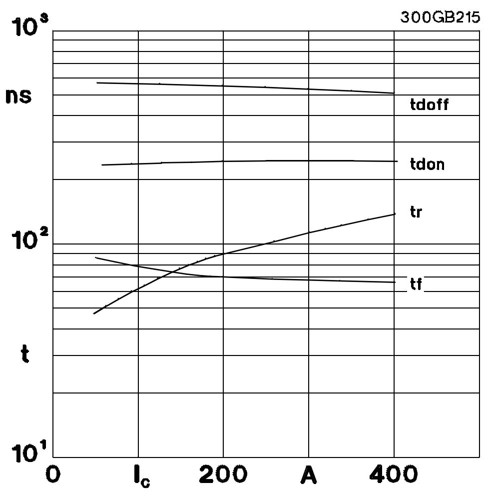
I_{Cpuls} = 300 A

Fig. 13 Typ. gate charge characteristic



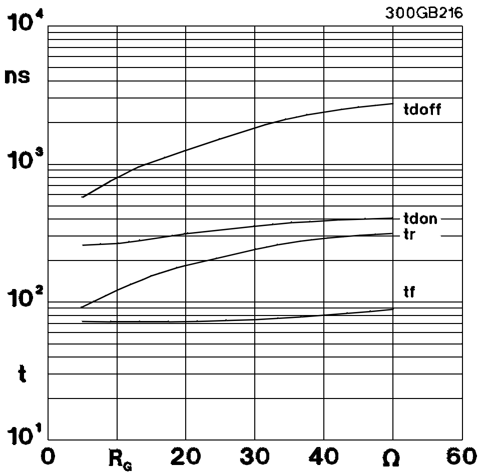
V_{GE} = 0 V
f = 1 MHZ

Fig. 14 Typ. capacitances vs.V_{CE}



T_j = 125 °C
V_{CE} = 600 V
V_{GE} = ± 15 V
R_{Gon} = 4,7 Ω
R_{Goff} = 4,7 Ω
induct. load

Fig. 15 Typ. switching times vs. I_C



T_j = 125 °C
V_{CE} = 600 V
V_{GE} = ± 15 V
I_C = 200 A
induct. load

Fig. 16 Typ. switching times vs. gate resistor R_G

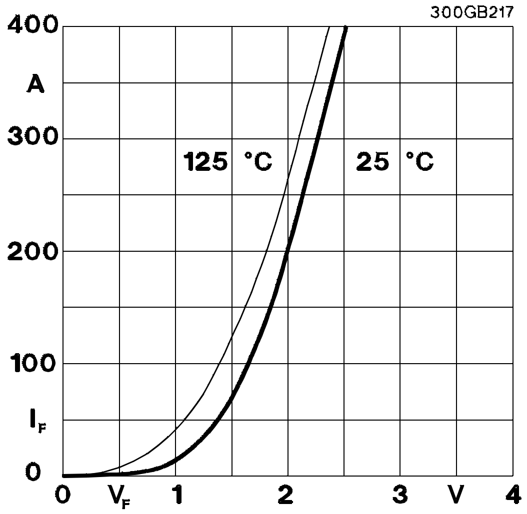


Fig. 17 Typ. CAL diode forward characteristic

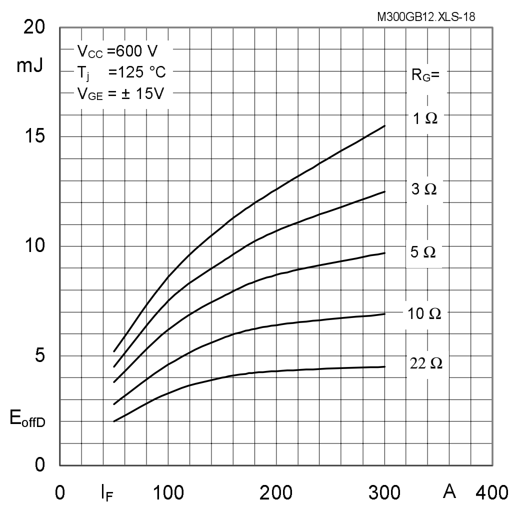


Fig. 18 Diode turn-off energy dissipation per pulse

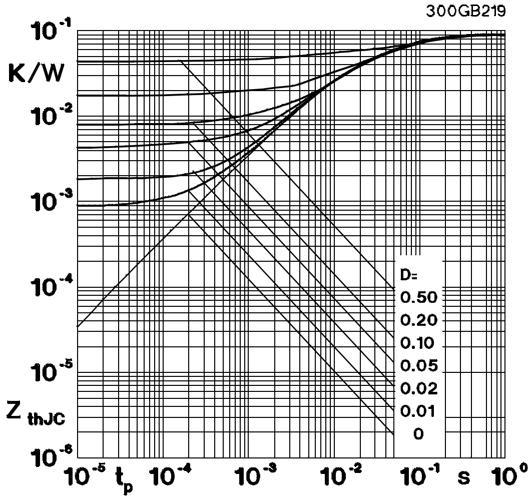


Fig. 19 Transient thermal impedance of IGBT $Z_{thJC} = f(t_p)$; $D = t_p / t_c = t_p \cdot f$

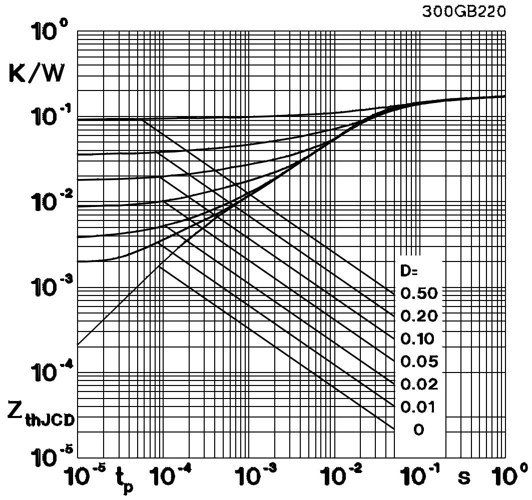


Fig. 20 Transient thermal impedance of inverse CAL diodes $Z_{thJCD} = f(t_p)$;

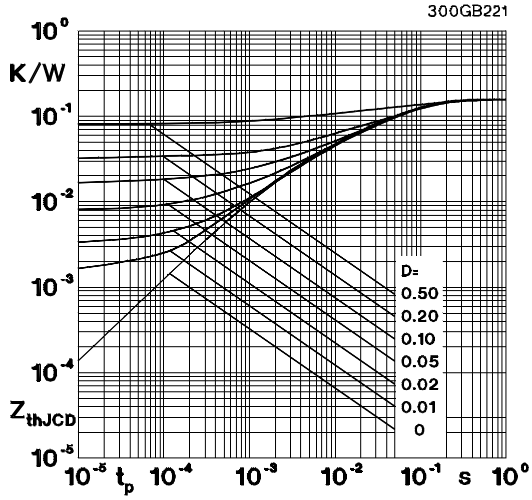


Fig. 21 Transient thermal impedance of the freewheeling diode $Z_{thjCD} \rightarrow$ B 6 – 169, rem. 6)

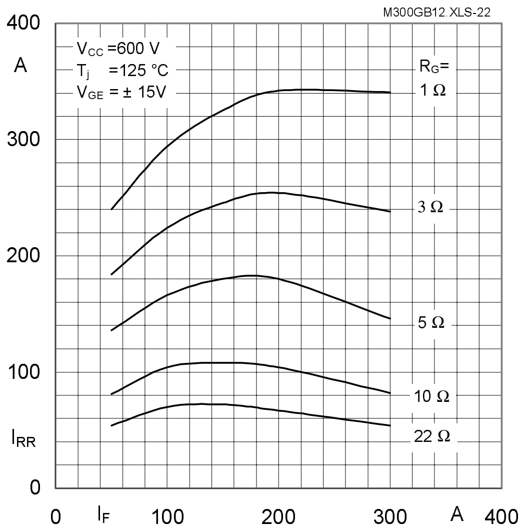


Fig. 22 Typ CAL diode reverse recovery current $I_{RR} = f(I_F; R_G)$

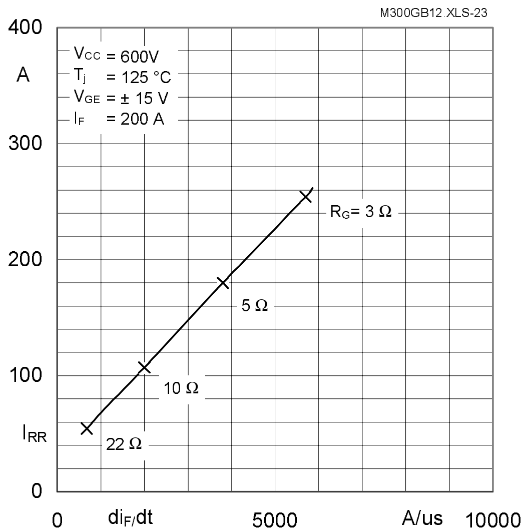


Fig. 23 Typ. CAL diode reverse recovery current $I_{RR} = f(di_F/dt; R_G)$

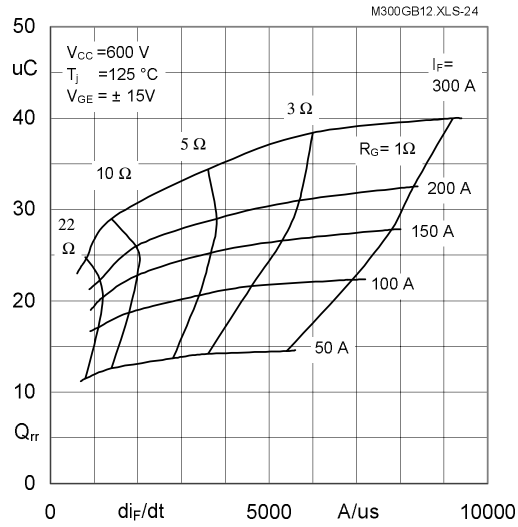


Fig. 24 Typ. CAL diode recovered charge $Q_{rr} = f(di_F/dt; I_F; R_G)$

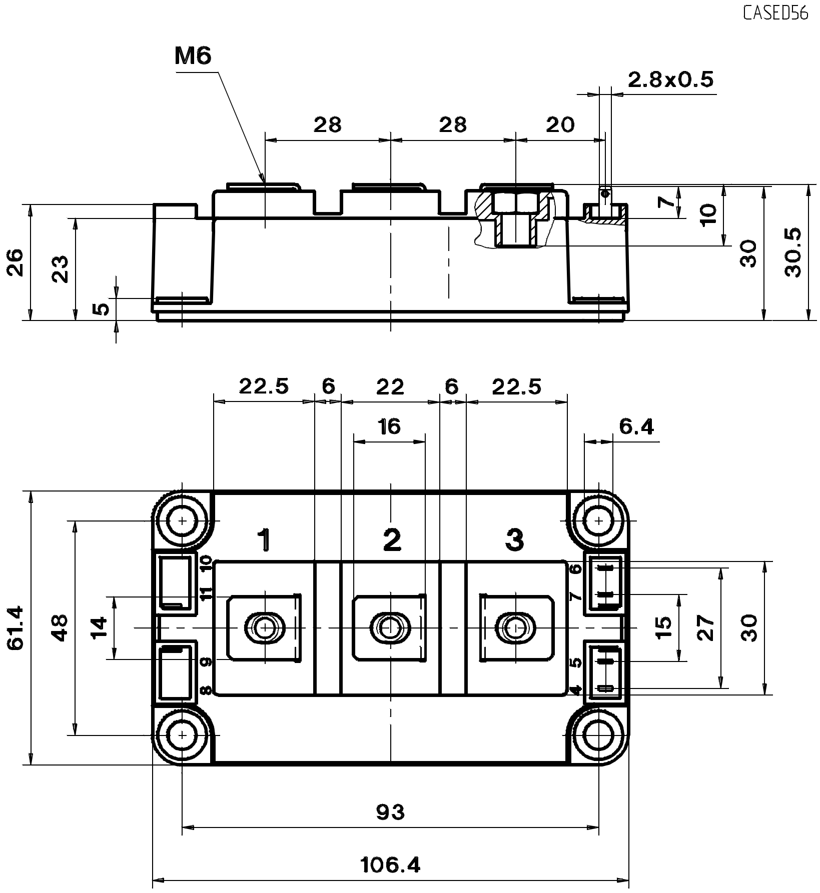
SEMITRANS 3

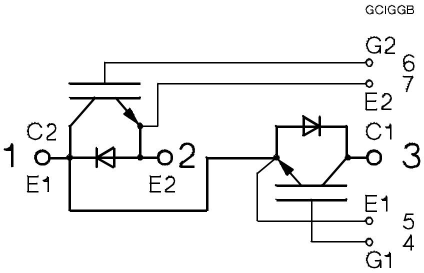
Case D 56

UL Recognized

File no. E 63 532

SKM 300 GB 123 D

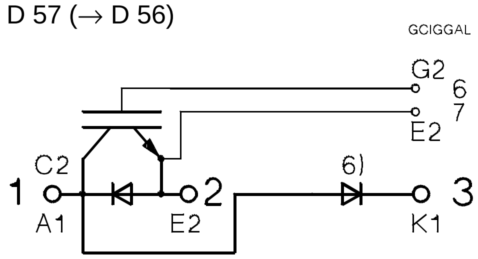




Dimensions in mm

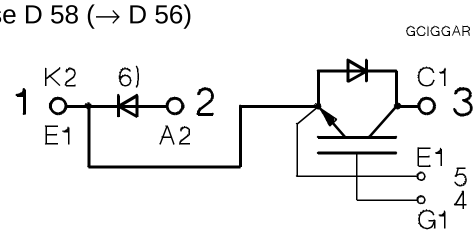
SKM 300 GAL 123 D

Case D 57 (→ D 56)



SKM 300 GAR 123 D

Case D 58 (→ D 56)



Case outline and circuit diagrams

Mechanical Data

Symbol	Conditions		Values min.	Values typ.	Values max.	Units
M_1	to heatsink, SI Units	(M6)	3	–	5	Nm
	to heatsink, US Units		27	–	44	lb.in.
M_2	for terminals, SI Units	(M6)	2,5	–	5	Nm
	for terminals US Units		22	–	44	lb.in.
a			–	–	5x9,81	m/s^2
w			–	–	325	g

This is an electrostatic discharge sensitive device (ESDS). Please observe the international standard IEC 747-1, Chapter IX.

Three devices are supplied in one SEMIBOX A without mounting hardware, which can be ordered separately under Ident No. 33321100 (for 10 SEMITRANS 3). Larger packing units of 12 and 20 pieces are used if suitable

Accessories → B 6 - 4.
SEMIBOX → C - 1.

6) Freewheeling diode → B 6 - 169, remark 6.

